

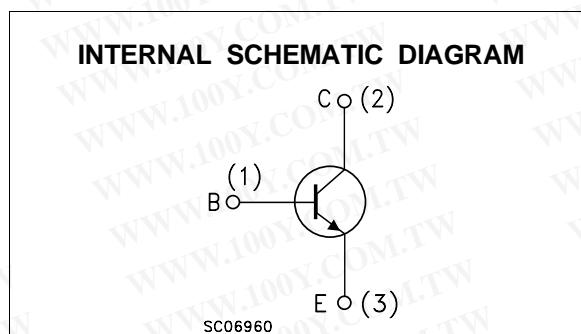
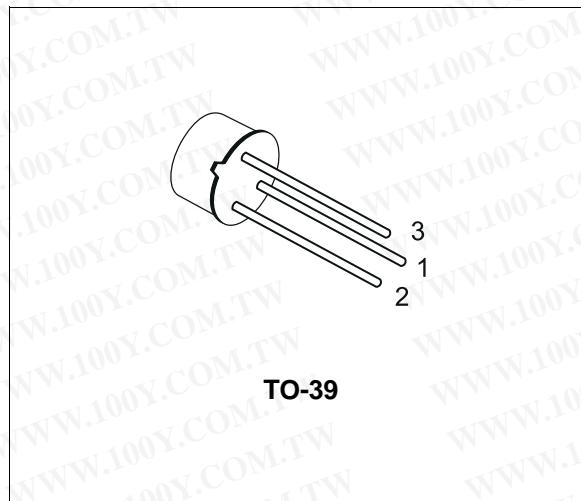


**2N3019**

## SMALL SIGNAL NPN TRANSISTOR

### DESCRIPTION

The 2N3019 is a silicon Planar Epitaxial NPN transistor in Jedec TO-39 metal case, designed for high-current, high frequency amplifier application. It feature high gain and low saturation voltage.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	140	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	80	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	7	V
$I_C$	Collector Current	1	A
$P_{tot}$	Total Dissipation at $T_{amb} \leq 25^\circ C$ at $T_C \leq 25^\circ C$	0.8 5	W W
$T_{stg}$	Storage Temperature	-65 to 175	°C
$T_j$	Max. Operating Junction Temperature	175	°C

**2N3019**

### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-Case	Max	30	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-Ambient	Max	187.5	°C/W

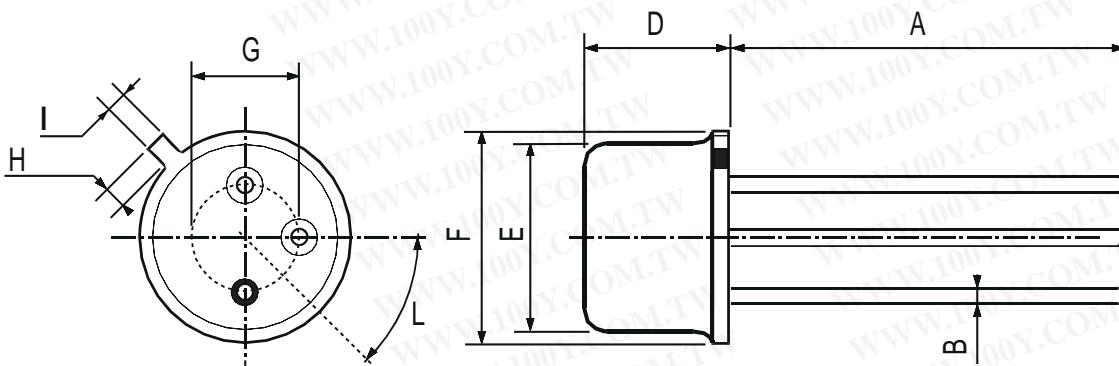
### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-off Current ( $I_E = 0$ )	$V_{CB} = 90\text{ V}$ $V_{CB} = 90\text{ V}$ $T_C = 150^\circ\text{C}$			10 10	nA μA
I <sub>EBO</sub>	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = 5\text{ V}$			10	nA
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage ( $I_E = 0$ )	$I_C = 100\text{ μA}$	140			V
V <sub>(BR)CEO*</sub>	Collector-Emitter Breakdown Voltage ( $I_B = 0$ )	$I_C = 10\text{ mA}$	80			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage ( $I_C = 0$ )	$I_E = 100\text{ μA}$	7			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	$I_C = 150\text{ mA}$ $I_B = 15\text{ mA}$ $I_C = 500\text{ mA}$ $I_B = 50\text{ mA}$			0.2 0.5	V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	$I_C = 150\text{ mA}$ $I_B = 15\text{ mA}$			1.1	V
$h_{FE}^*$	DC Current Gain	$I_C = 0.1\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}$ $V_{CE} = 10\text{ V}$ $I_C = 1\text{ A}$ $V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}$ $V_{CE} = 10\text{ V}$ $T_{amb} = -55^\circ\text{C}$	50 90 100 50 15 40		300	
$h_{fe}^*$	Small Signal Current Gain	$I_C = 1\text{ mA}$ $V_{CE} = 5\text{ V}$ $f = 1\text{ KHz}$	80		400	
f <sub>T</sub>	Transition Frequency	$I_C = 50\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 20\text{ MHz}$	100			MHz
C <sub>CBO</sub>	Collector-Base Capacitance	$I_E = 0$ $V_{CB} = 10\text{ V}$ $f = 1\text{ MHz}$			12	pF
C <sub>EBO</sub>	Emitter-Base Capacitance	$I_C = 0$ $V_{EB} = 0.5\text{ V}$ $f = 1\text{ MHz}$			60	pF
NF	Noise Figure	$I_C = 0.1\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 1\text{ KHz}$ $R_g = 1\text{ k}\Omega$			4	dB
r <sub>bb' C<sub>b'c</sub></sub>	Feedback Time Constant	$I_C = 10\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 4\text{ MHz}$			400	ps

\* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 1 %

**TO-39 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



P008B